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| Terms | Documents |
|---|-----------|
| (silicon adj nitride) same (C4F6 or C5F8) same etch\$ | 1 |

Database:

- US Patents Full-Text Database
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- JPO Abstracts Database
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side by side**Hit Count Set Name**
result set*DB=USPT; PLUR=YES; OP=ADJ*L1 (silicon adj nitride) same (C4F6 or C5F8) same etch\$0 L1*DB=DWPI; PLUR=YES; OP=ADJ*L2 (silicon adj nitride) same (C4F6 or C5F8) same etch\$2 L2*DB=PGPB; PLUR=YES; OP=ADJ*L3 (silicon adj nitride) same (C4F6 or C5F8) same etch\$1 L3

END OF SEARCH HISTORY

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Search Results - Record(s) 1 through 2 of 2 returned.☐ 1. Document ID: KR 2001046792 A

L2: Entry 1 of 2

File: DWPI

Jun 15, 2001

DERWENT-ACC-NO: 2002-087444

DERWENT-WEEK: 200212

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TITLE: Method for forming self-aligned contact hole of semiconductor device

Basic Abstract Text:

DETAILED DESCRIPTION - In the method, after a gate electrode(43) having a polysilicon layer(38), a tungsten silicide(40) and a silicon nitride layer(42) are formed on a semiconductor substrate(30), a spacer(44) is formed from undoped silicate glass(USG) on a sidewall of the gate electrode(43). An interlayer dielectric layer(45) is then formed over the substrate(30) and etched by using an etching gas in which an etch selectivity of the interlayer dielectric layer(45) to the spacer(44) is 15:1 or more. The interlayer dielectric layer(45) is formed from borophospho silicate glass(BPSG) or phospho silicate glass(PSG). The etching gas is preferably composed of C5F8, CH2F2, O2 and Ar, which are mixed with a flow rate of 2:1:2:50.

Basic Abstract Text (2):

DETAILED DESCRIPTION - In the method, after a gate electrode(43) having a polysilicon layer(38), a tungsten silicide(40) and a silicon nitride layer(42) are formed on a semiconductor substrate(30), a spacer(44) is formed from undoped silicate glass(USG) on a sidewall of the gate electrode(43). An interlayer dielectric layer(45) is then formed over the substrate(30) and etched by using an etching gas in which an etch selectivity of the interlayer dielectric layer(45) to the spacer(44) is 15:1 or more. The interlayer dielectric layer(45) is formed from borophospho silicate glass(BPSG) or phospho silicate glass(PSG). The etching gas is preferably composed of C5F8, CH2F2, O2 and Ar, which are mixed with a flow rate of 2:1:2:50.

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC |
|-----------|-------|----------|-------|--------|----------------|------|-----------|-----------|-------------|--------|------|
| Draw Desc | Image | | | | | | | | | | |

☐ 2. Document ID: JP 2000349071 A

L2: Entry 2 of 2

File: DWPI

Dec 15, 2000

DERWENT-ACC-NO: 2001-185436

DERWENT-WEEK: 200119

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TITLE: Chemical dry etching procedure for semiconductor device, involves etching film by activation of mixed gas on semiconductor substrate

Basic Abstract Text:

NOVELTY - The method involves etching the film by activation of mixed gas containing oxygen, nitrogen and octafluoro cyclopentene (C5F8) on the semiconductor substrate (9) in the etching chamber (5). The film that is etched is a photoresist film, polysilicon film or silicon nitride film.

Basic Abstract Text (1):

NOVELTY - The method involves etching the film by activation of mixed gas containing oxygen, nitrogen and octafluoro cyclopentene (C5F8) on the semiconductor substrate (9) in the etching chamber (5). The film that is etched is a photoresist film, polysilicon film or silicon nitride film.

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC |
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| Terms | Documents |
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| (silicon adj nitride) same (C4F6 or C5F8) same etch\$ | 2 |

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WEST[Generate Collection](#)[Print](#)**Search Results - Record(s) 1 through 1 of 1 returned.**☐ 1. Document ID: US 20020039843 A1

L3: Entry 1 of 1

File: PGPB

Apr 4, 2002

PGPUB-DOCUMENT-NUMBER: 20020039843

PGPUB-FILING-TYPE: new

DOCUMENT-IDENTIFIER: US 20020039843 A1

TITLE: Method of manufacturing a semiconductor integrated circuit device

PUBLICATION-DATE: April 4, 2002

INVENTOR-INFORMATION:

| NAME | CITY | STATE | COUNTRY | RULE-47 |
|--------------------|------------|-------|---------|---------|
| Ikeda, Takenobu | Ome | | JP | |
| Tadokoro, Masahiro | Hachioji | | JP | |
| Izawa, Masaru | Hino | | JP | |
| Yunogami, Takashi | Sagamihara | | JP | |

US-CL-CURRENT: 438/738

| Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments |
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| Terms | Documents |
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